Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	13477	silicon adj oxide with coat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:09
L7	38107	silicon near2 coat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:20
L8	5481	6 and 7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:09
L9	4473	silicon adj coat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:20
L10	157072	silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:20
L11	161	9 with 10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:21
L12	7583	(semiconductor wafer) with laser with etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:21
L13	1	11 and 12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:21
L16	722	interposer with silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:30

L17	32	interposer with silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:33
L18	83	silicon adj oxide adj coated adj silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:34
L19	19	silicon adj oxide adj coated adj silicon same interpos\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:35
L20	33415	interpos\$4 with (resin plastic glass insulat\$5) with (form\$3 manufactur\$4 made)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:39
L21	7059	interpos\$4 with (resin plastic glass insulat\$5) with (form\$3 manufactur\$4 made) same (interpos\$4 with (semiconduct\$3 die))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:40
L22	54	interpos\$4 with (resin plastic glass insulat\$5) with (form\$3 manufactur\$4 made) same (interpos\$4 with (semiconduct\$3 die)) and (interpos\$4 near5 silicon adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:43
L23	1	interpos\$4 with (resin plastic glass insulat\$5) with (form\$3 manufactur\$4 made) same (interpos\$4 with (semiconduct\$3 die)) and (interpos\$4 near5 silicon adj oxide) same interposer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:43
L24	0	interpos\$4 with (resin plastic glass insulat\$5) with (form\$3 manufactur\$4 made) same (interpos\$4 with (semiconduct\$3 die)) and (interpos\$4 near5 silicon adj oxide) and interposer not 23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:44
L25	31	interpos\$4 with (resin plastic glass insulat\$5 oxide) same (interpos\$4 with (semiconduct\$3 die)) and (interpos\$4 with silicon adj oxide) and interposer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:56

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L26	27	25 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:54
L27	1	("6507497").PN.	USPAT; USOCR	OR	OFF	2007/05/25 09:56
L28	1	27 and interpos\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:57
L29	0	27 and interpos\$4 and (insulat\$4 with silcon with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2007/05/25 09:58
L30	0	27 and interpos\$4 and (silcon with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 09:58
L31	1	27 and interpos\$4 and (oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 10:11
L32	1743	interposer.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 10:11
L33	42	32 and silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 10:12
L34	28	32 and silicon adj oxide same interpos\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 10:25
L35	1	("6608259").PN.	USPAT; USOCR	OR	OFF	2007/05/25 10:25
L36	0	("35andsiliconadjoxide").PN.	USPAT; USOCR	OŖ	OFF	2007/05/25 10:25

L37	1	35 and silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 10:26
L38	1	35 and silicon adj oxide and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 10:26